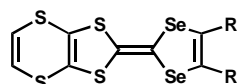


X or Acceptor	D : A	$\sigma_{\text{rt}} / \text{Scm}^{-1}$ (試料形状)	T_c / K [種類]	ref.	構造ref.	磁性ref.
Au(CN) ₂	2:1	2500 (s)	0.8 (5kbar) [SC]	1	9	17, 18
AuCl ₂	2:1	100 (s)	0.83 [SC]	2	12	
AuBr ₂	2:1	13 (s)	1.6 (1.5kbar) [SC]	3	6	18
AuBr ₂	2:1	200 (s)	1.9 [SC]	4	6	18
AuI ₂	2:1	300 (s)	0.55 (5kbar) [SC]	2	11	
I ₃	2:1	160 (s)	0.47 [SC]	5	13	18
IBr ₂	2:1	210 (s)	0.58 [SC]	5	10	
I ₂ Br	2:1	320 (s)	[M]	6		
BF ₄	2:1	130 (s)	40 [M-I]	7	10, 14	18
ClO ₄	2:1	260 (s)	32 [M-I]	6	15	19
ReO ₄	2:1	40 (s)	295 [M-I]	8	8	
FeBr ₄	2:1	14 (s)	200 [M-I]	16	16	16
PF ₆	2:1	300 (s)	semicond.	7	7	18
AsF ₆	2:1	200 (s)	semicond.	7		
SCN	2:1	80 (s)	[M]	6		

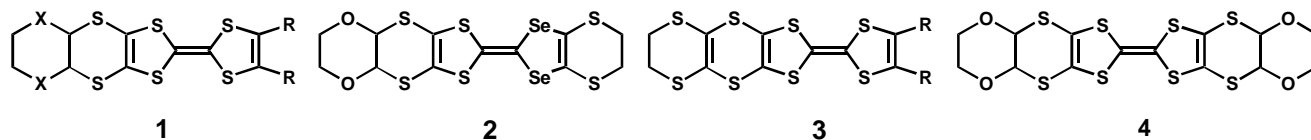
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R	X or Acceptor	D : A	$\sigma_{\text{rt}} / \text{Scm}^{-1}$ (試料形状)	T_c / K [種類]	ref.	構造ref.	磁性ref.
CH ₃	I ₃	2:1	0.19 (s)	semicond.	1		
	AuCl ₂	1:1	0.64 (s)	semicond.	1		
	AuI ₂	3:2	3.2 (s)	semicond.	1		
	ClO ₄		6.1x10 ⁻⁴ (s)	semicond.	1		
	PF ₆	5:2	1.2x10 ⁻² (s)	semicond.	1		
-(CH ₂) ₃ -	I ₃	5:2	13 (p)	260 [M-I]	1		
	AuI ₂	2:1	21 (p)	220 [M-I]	1		
	ClO ₄	2:1	135 (s)	M	2	2	2
	PF ₆	2:1	620 (s)	M	1	1	
	AsF ₆	2:1	125 (s)	M	2	2	2
-S(CH ₂) ₂ S-	I ₃	9:2	0.17 (s)	semicond.	1		
	PF ₆	5:2	13 (s)	M	1		

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R	X	X or Acceptor	D : A	$\sigma_{\text{rt}} / \text{Scm}^{-1}$ (試料形状)	T_c / K [種類]	ref.	構造ref.	磁性ref.
1 -S(CH ₂) ₂ S-	O	Cl ₂ Br	3:1	2.9 (p)	semicond.	1		
		Br ₂ Cl	4:1	2.4 (p)	semicond.	1		
		Br ₃	3:1	<10 ⁻⁶ (p)		1		
		Br ₂ I	5:3	<10 ⁻⁶ (p)		1		
		I ₂ Br	5:3	1.2 (p)	semicond.	1		
		I ₃	1:1	2.2 (s)	semicond.	1		
		Au(CN) ₂	2:1	13 (s)	30 [M-I]	1		
		AuCl ₂	1:1	12 (p)	semicond.	1		
		AuI ₂	1:1	0.033 (p)	semicond.	1		
		BF ₄	2:1	27 (s)	100 [M-I]	1	1	
		ClO ₄		1.0 (p)	semicond.	1		
		ReO ₄	3:1	0.43 (p)	semicond.	1		
		PF ₆	2:1	0.95 (p)	semicond.	1		
		AsF ₆	2:1	0.35 (p)	semicond.	1		
		SbF ₆	2:1	0.63 (s)	semicond.	1		
TCNQ	1:1	<10 ⁻⁶ (p)		3				
-S(CH ₂) ₂ S-	S	TCNQ	5:1	0.014 (p)	semicond.	3		
		-Se(CH ₂) ₂ Se-	O	I ₃ (needle)	2:1	60 (s)	250 [M-I]	2
I ₃ (plate)	2:0.8	20 (s)		45 [M-I]	5			
AuI ₂	2:0.75	1.4 (s)		55 [M-I]	2	2		
BF ₄	3:2	5.0 (s)		semicond.	2			
ClO ₄	2:1	2.3 (s)		semicond.	2			
PF ₆	2:1	0.62 (s)		semicond.	2			
AsF ₆	5:2	5.1 (s)		semicond.	2			
TCNQ		<10 ⁻⁶ (p)			2			
-SeCH ₂ Se-	O	I ₃		2:1	4.6x10 ⁻² (s)	semicond.	4	

		AuI ₂	3:2	0.11 (s)	semicond.	4			
		BF ₄	2:1	9.8x10 ⁻⁴ (s)	semicond.	4			
		CIO ₄	2:1	9.4x10 ⁻⁵ (s)	semicond.	4			
		PF ₆	2:1	2.6x10 ⁻⁷ (s)	semicond.	4			
		AsF ₆	2:1	6.0 (s)	M	4			
	-O(CH ₂) ₂ O-	I ₃	1:1	4.5x10 ⁻⁷ (p)	semicond.	5			
	O	Au(CN) ₂	2:1	227 (s)	M	5			
		BF ₄	2:1	27 (s)	M	6	6		
		PF ₆	2:1	173 (s)	M	5			
2		I ₃	4:3	<10 ⁻⁶ (p)		5			
		BF ₄		3.2 (p)	semicond.	5			
		PF ₆	3:1	12 (p)	semicond.	5			
3	-S(CH ₂) ₂ S-	TCNQ	1:1	0.068 (p)	semicond.	3			
		I ₃		0.43	semicond.	3			
		AuI ₂		0.012	semicond.	7			
		CIO ₄		1.2 (p)	semicond.	3			
		BF ₄		0.0049	semicond.	7			
		AsF ₆		0.29	semicond.	7			
		SbF ₆		0.29	semicond.	7			
		Cu(NCS) ₂		0.019 (p)	semicond.	3			
4		I ₃	2:1			8	8	8	

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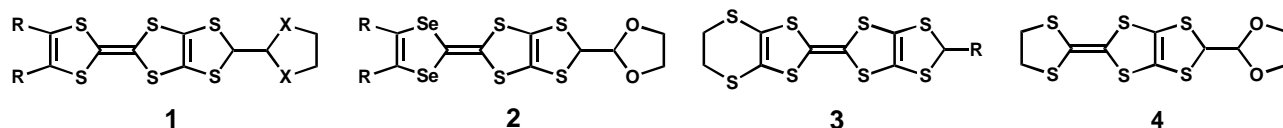
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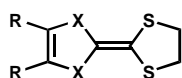
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	R	X	X or Acceptor	D : A	$\sigma_{\text{rt}} / \text{Scm}^{-1}$ (試料形状)	T _c / K [種類]	ref.	構造ref.	磁性ref.
1	H	O	TCNQ	5:4	9.1 (p)	semicond.	1		
	-S(CH ₂) ₂ S-	O	TCNQ	1:1	12 (p)	~ 150 [M-I]	1		
	-S(CH ₂) ₂ S-	S	I ₃	3:1	0.32 (p)	semicond.	2, 4		
			AuI ₂	5:3	13 (s)	35 [M-I]	2, 4		
			BF ₄	2:1	7.0 (s)	110 [M-I]	2, 4		
			CIO ₄		0.095 (p)	semicond.	2, 4		
			AsF ₆	3:1	19 (s)	60 [M-I]	2, 4		
		TCNQ		<10 ⁻⁶ (s)		2			
2			TCNQ	1:2	<10 ⁻⁶ (p)		1		
3	Me		AuI ₂	5:2	8.1x10 ⁻³ (s)	semicond.	3		
			BF ₄	3:2	5.5x10 ⁻⁴ (s)	semicond.	3		

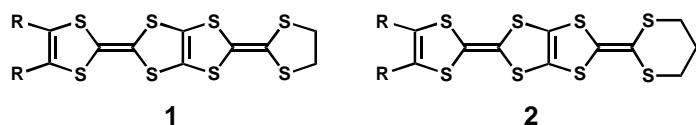
	CIO ₄		4.2x10 ⁻³ (s)	semicond.	3
	PF ₆	5:2	1.4x10 ⁻³ (s)	semicond.	3
Et	AuI ₂	1:1	1.3x10 ⁻³ (p)	semicond.	3
	BF ₄	5:2	2.5 (p)	semicond.	3
	CIO ₄		26 (p)	~ 230 [M-I]	3
	PF ₆	5:2	17 (p)	~ 170 [M-I]	3
4	TCNQ	1:2	<10 ⁻⁶ (p)		1

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R	X	X or Acceptor	D : A	$\sigma_{rt} / \text{Scm}^{-1}$ (試料形状)	T _c / K [種類]	ref.	構造ref.	磁性ref.
-SCH ₂ S-	S	AuCl ₂	5:2	5.8x10 ⁻² (p)	semicond.	1		
		AuI ₂	2:1	60 (s)	M	1		
		BF ₄	7:2	3.7x10 ⁻³ (p)	semicond.	1		
		TCNQ		<10 ⁻⁶ (s)		1		
-S(CH ₂) ₂ S-	S	I ₃ (TCE)	1:1	<10 ⁻⁶ (s)		1		
		I ₃ (o-C ₆ H ₄ Cl ₂)	10:9	1.2x10 ⁻³ (s)	semicond.	1		
		BF ₄	3:2	7.8x10 ⁻² (p)	semicond.	1		
		CIO ₄	3:2	1.4x10 ⁻² (p)	semicond.	1		
		ReO ₄	5:4	1.3x10 ⁻⁴ (p)	semicond.	1		
		PF ₆	2:1	<10 ⁻⁶ (s)		1		
		AsF ₆	1:1	<10 ⁻⁶ (s)		1		
		TCNQ		<10 ⁻⁶ (s)		1		
-SCH=CHS-		BF ₄	4:3	5.2x10 ⁻³ (p)	semicond.	1		
		CIO ₄		3.4x10 ⁻³ (p)	semicond.	1		
		TCNQ		<10 ⁻⁶ (s)		1		
CH ₃	Se	CIO ₄	2:1	<10 ⁻⁶ (p)	semicond.	1		
		TCNQ		<10 ⁻⁶ (s)		1		
-(CH ₂) ₃ -		CIO ₄	2:1	<10 ⁻⁶ (p)	semicond.	1		
		TCNQ		<10 ⁻⁶ (s)		1		
-S(CH ₂) ₂ S-		BF ₄	3:2	8.9x10 ⁻² (p)	semicond.	1		
		CIO ₄	5:3	2.3 (p)	semicond.	1		
		ReO ₄	3:2	1.0 (p)	semicond.	1		

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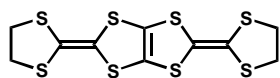
	R	X or Acceptor	D : A	$\sigma_{rt} / \text{Scm}^{-1}$ (試料形状)	T _c / K [種類]	ref.	構造ref.	磁性ref.
1	H	TCNQ	1:1	45 (p)	110 [M-I]	1, 2		

		AuI ₂	5:4	450 (s)	M	1, 2	
		ClO ₄		17 (s)	32 [M-I]	1, 2	
		AsF ₆	5:4	4.2 (p)	150 [M-I]	1, 2	
	SMe	TCNQ	1:1	0.08 (p)	semicond.	1, 2	
		I ₃	4:1	7.0 (s)	semicond.	1, 2	
		BF ₄	5:2	33 (s)	semicond.	1, 2	
		ClO ₄		22 (s)	semicond.	1, 2	
		PF ₆	5:2	130 (s)	M	1, 2	
		AsF ₆	5:2	170 (s)	M	1, 2	
	-S(CH ₂) ₂ S-	TCNQ	5:3	8.6 (p)	semicond.	1, 2	
		I ₃	5:2	9.6 (p)	160 [M-I]	1, 2	
		AuI ₂	2:1	14 (s)	M	1, 2	1
		BF ₄	2:1	2.3 (p)	semicond.	1, 2	
		ClO ₄		18 (p)	semicond.	1, 2	
		PF ₆	2:1	58 (s)	M	1, 2	
		AsF ₆	2:1	16 (s)	M	1, 2	
	-SCH ₂ S-	I ₃	2:1	3.1 (p)	semicond.	1, 2	
		AuI ₂	2:1	1.3 (p)	semicond.	1, 2	
2	H	TCNQ	5:4	7.8 (p)	semicond.	2, 3	
		I ₃	2:1	0.85 (p)	semicond.	2, 3	
		AuI ₂	2:1	1.9 (p)	semicond.	2, 3	
		ClO ₄		2.0 (p)	semicond.	2, 3	
		AsF ₆	5:3	1.2 (p)	semicond.	2, 3	
	SMe	TCNQ	5:4	13 (p)	semicond.	2, 3	
		I ₃	3:2	3.9 (p)	semicond.	2, 3	
		AuI ₂	2:1	710 (s)	250 [M-I]	2, 3	
		ClO ₄		0.46 (s)	semicond.	2, 3	
		AsF ₆	3:2	11 (s)	semicond.	2, 3	
	-S(CH ₂) ₂ S-	I ₃	2:1	1.1 (p)	semicond.	2, 3	
		AuI ₂	2:1	36 (p)	165 [M-I]	2, 3	3
		BF ₄	2:1	52 (p)	170 [M-I]	2, 3	
		ClO ₄		21 (p)	125 [M-I]	2, 3	
		PF ₆	2:1	44 (p)	60 [M-I]	2, 3	
		AsF ₆	3:2	12 (p)	95 [M-I]	2, 3	
	-SCH ₂ S-	AuI ₂	2:1	71 (p)	215 [M-I]	2, 3	
		ClO ₄		0.018 (p)	semicond.	2, 3	
		AsF ₆	1:1	0.037 (p)	semicond.	2, 3	

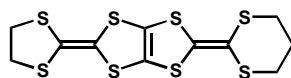
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1



2

	X or Acceptor	D : A	$\sigma_{rt} / \text{Scm}^{-1}$ (試料形状)	T _c / K [種類]	ref.	構造ref.	磁性ref.
1	TCNQ	1:1	2.0x10 ⁻⁷ (s)	semicond.	1		
	TCNQF ₄	3:2	5.6x10 ⁻⁵ (p)	semicond.	1		

	I ₃	2:1	230	M	1	
	AuI ₂	2:1	49	M	1	
	BF ₄	2:1	33	M	1	
	ClO ₄		106	M	1	
	PF ₆	2:1	102	M	1	1
	AsF ₆	2:1	49	M	1	
2	I ₃	3:1	53	M	3	
	BF ₄	2:1	2.3	M	3	
	ClO ₄		0.42	semicond.	3	
	AsF ₆	2:1	0.15	semicond.	3	

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